

P-Channel 2.5 V (G-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^b
- 20	0.100 at $V_{GS} = - 4.5$ V	- 2.4
	0.150 at $V_{GS} = - 2.5$ V	- 2.0

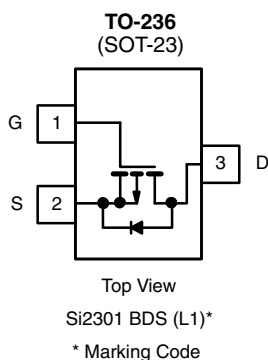
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS*
COMPLIANT

HALOGEN
FREE
Available



Ordering Information: Si2301BDS-T1-E3 (Lead (Pb)-free)
Si2301BDS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

Parameter	Symbol	5 s	Steady State	Unit
Drain-Source Voltage	V_{DS}	- 20		V
Gate-Source Voltage	V_{GS}	± 8		
Continuous Drain Current ($T_J = 150$ °C) ^b	I_D	- 2.4	- 2.2	A
		- 1.9	- 1.8	
Pulsed Drain Current ^a	I_{DM}	- 10		
Continuous Source Current (Diode Conduction) ^b	I_S	- 0.72	- 0.6	
Power Dissipation ^b	P_D	0.9	0.7	W
		0.57	0.45	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^b	R_{thJA}	120	145	°C/W
Maximum Junction-to-Ambient ^c		140	175	

Notes:

- a. Pulse width limited by maximum junction temperature.
b. Surface mounted on FR4 board, $t \leq 5$ s.
c. Surface mounted on FR4 board.

* Pb containing terminations are not RoHS compliant, exemptions may apply.

SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

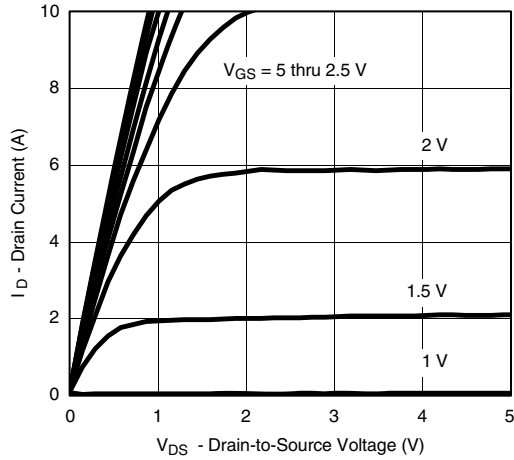
Parameter	Symbol	Test Conditions	Limits			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = -250\text{ }\mu\text{A}$	- 20			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\text{ }\mu\text{A}$	- 0.45		- 0.95	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 8\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -20\text{ V}$, $V_{GS} = 0\text{ V}$			- 1	μA
		$V_{DS} = -20\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 55\text{ }^{\circ}\text{C}$			- 10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq -5\text{ V}$, $V_{GS} = -4.5\text{ V}$	- 6			A
		$V_{DS} \leq -5\text{ V}$, $V_{GS} = -2.5\text{ V}$	- 3			
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}$, $I_D = -2.8\text{ A}$		0.080	0.100	Ω
		$V_{GS} = -2.5\text{ V}$, $I_D = -2\text{ A}$		0.110	0.150	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -5\text{ V}$, $I_D = -2.8\text{ A}$		6.5		S
Diode Forward Voltage	V_{SD}	$I_S = -0.75\text{ A}$, $V_{GS} = 0\text{ V}$		- 0.80	- 1.2	V
Dynamic ^b						
Total Gate Charge	Q_g	$V_{DS} = -6\text{ V}$, $V_{GS} = -4.5\text{ V}$ $I_D \cong -2.8\text{ A}$		4.5	10	nC
Gate-Source Charge	Q_{gs}			0.7		
Gate-Drain Charge	Q_{gd}			1.1		
Gate Resistance	R_g	$f = 1\text{ MHz}$	2	8	16	Ω
Input Capacitance	C_{iss}	$V_{DS} = -6\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$		375		pF
Output Capacitance	C_{oss}			95		
Reverse Transfer Capacitance	C_{rss}			65		
Switching ^c						
Turn-On Time	$t_{d(on)}$	$V_{DD} = -6\text{ V}$, $R_L = 6\text{ }\Omega$ $I_D \cong -1\text{ A}$, $V_{GEN} = -4.5\text{ V}$ $R_g = 6\text{ }\Omega$		20	30	ns
	t_r			40	60	
Turn-Off Time	$t_{d(off)}$			30	45	
	t_f			20	30	

Notes:

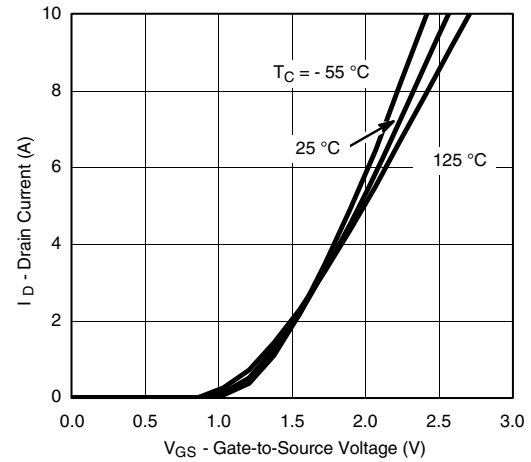
- a. Pulse test: pulse width $\leq 300\text{ }\mu\text{s}$ duty cycle $\leq 2\%$.
b. For DESIGN AID ONLY, not subject to production testing.
c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

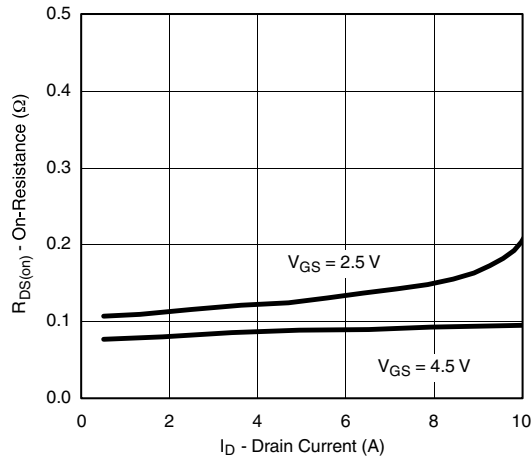
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



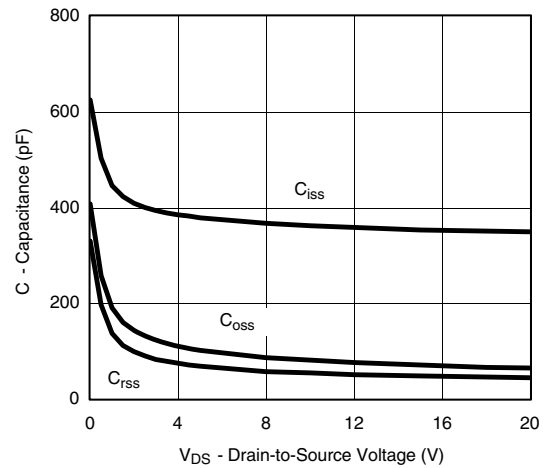
Output Characteristics



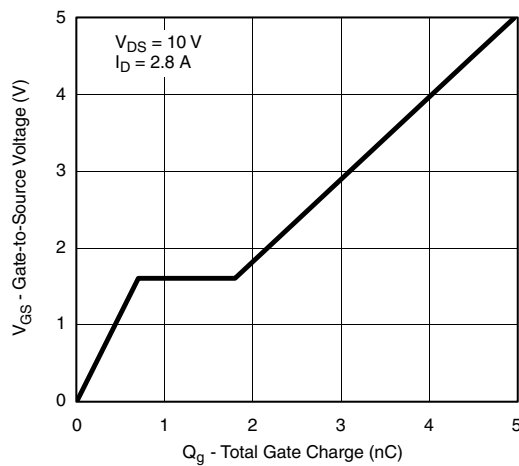
Transfer Characteristics



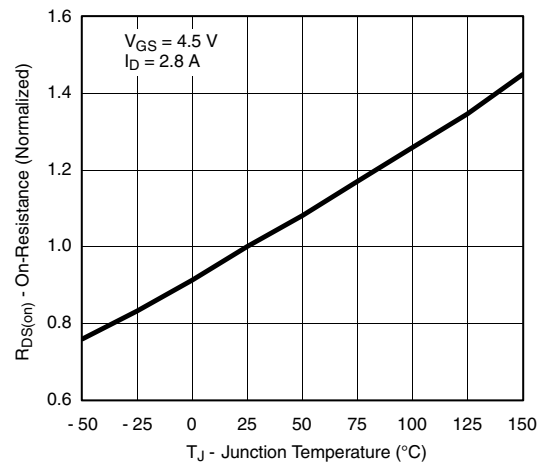
On-Resistance vs. Drain Current



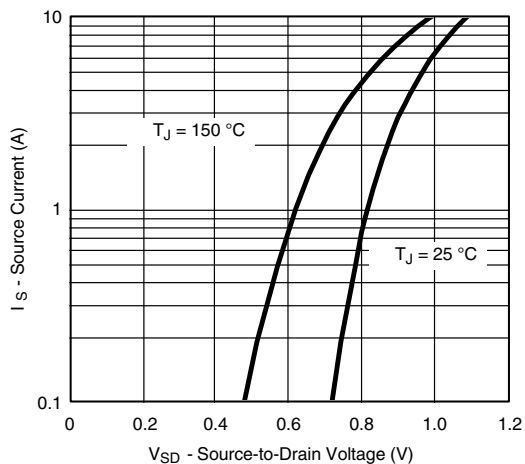
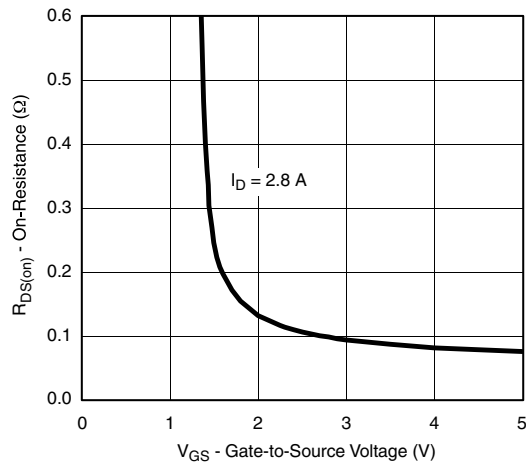
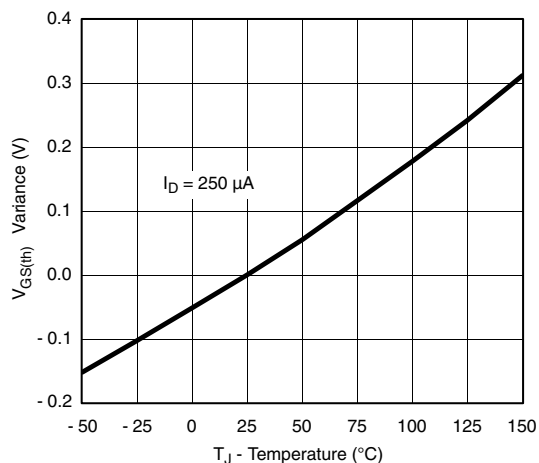
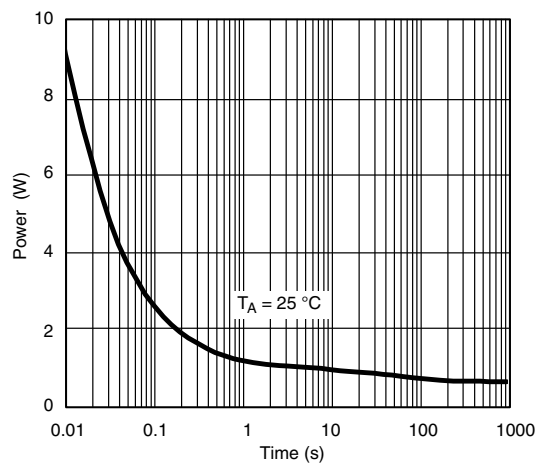
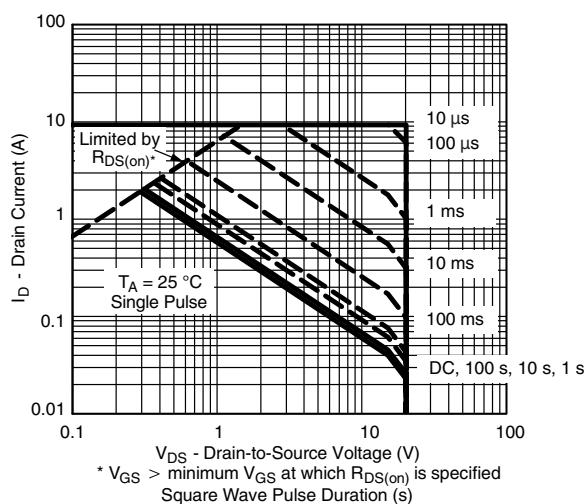
Capacitance



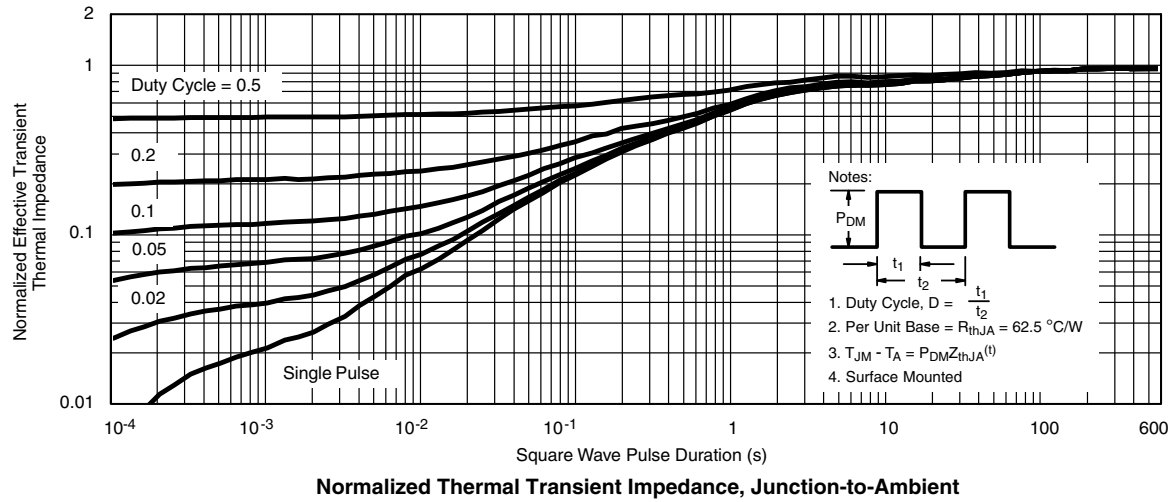
Gate Charge



On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power****Safe Operating Area**

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



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SOT-23 (TO-236): 3-LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A ₁	0.01	0.10	0.0004	0.004
A ₂	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E ₁	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e ₁	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L ₁	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°
ECN: S-03946-Rev. K, 09-Jul-01				
DWG: 5479				

RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads
Dimensions in Inches/(mm)

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